SEMICONDUCTOR DEVICE WITH BIASED FEATURE

ABSTRACT

A method of fabricating a semiconductor device includes forming a plurality of line element on a provided substrate. The plurality of line elements includes a first line element having a first region having a first width and a biased region having a second width. The second width different than the first width. Spacer elements are then formed abutting sidewalls of each of the plurality of line elements including the biased region where the spacer elements may be shifted. After forming the spacer elements, the plurality of line elements from the substrate are removed from the substrate. An underlying layer is etched using the spacer elements after removing the plurality of line elements.

Figure 5